

Appl. No. 09/817,963
Amdt. Dated February 17, 2004
Reply to Office Action of November 17, 2003

CLAIM AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-3 (Canceled).

4 (currently amended). A process for metallizing at least one insulating layer of an electronic or microelectronic component, which comprises:

applying at least one first insulating layer to a substrate such that the first insulating layer has a thickness not greater than 50 μ m;

activating all of the entire first insulating layer by treatment with an activator, the activator being at least one of a gas, a liquid, a solution, and a plasma;

then, after activating the entire first insulating layer, applying and patterning a second insulating layer made of a photosensitive material; and

Appl. No. 09/817,963
Amdt. Dated February 17, 2004
Reply to Office Action of November 17, 2003

then, after applying and patterning the second insulating layer, seeding and metallizing regions of the first insulating layer that are exposed by the patterning step.

5 (previously presented). The process according to claim 4, which comprises forming the first insulating layer and the second insulating layer from the same material.

6 (previously presented). The process according to claim 5, which comprises patterning the first insulating layer before the second insulating layer is applied.

7 (previously presented). The process according to claim 4, which comprises patterning the first insulating layer before the second insulating layer is applied.